

# J P Leitão

## List of Publications by Year in descending order

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Version: 2024-02-01

12

papers

436

citations

933447

10

h-index

1125743

13

g-index

13

all docs

13

docs citations

13

times ranked

631

citing authors

#	ARTICLE	IF	CITATIONS
1	Insights into recombination channels in a CVD grown ZnSe single crystal. <i>Applied Physics A: Materials Science and Processing</i> , 2022, 128, 1.	2.3	1
2	Mg-Doping of (111)B GaAs Thin Films Grown by Molecular Beam Epitaxy. <i>Journal of Physical Chemistry C</i> , 2019, 123, 12807-12812.	3.1	1
3	Fluctuating potentials in GaAs:Si nanowires: critical reduction of the influence of polytypism on the electronic structure. <i>Nanoscale</i> , 2018, 10, 3697-3708.	5.6	13
4	Insulator Materials for Interface Passivation of Cu(In,Ga)Se <sub>2</sub> Thin Films. <i>IEEE Journal of Photovoltaics</i> , 2018, 8, 1313-1319.	2.5	39
5	Synthesis and formation mechanism of CuInSe <sub>2</sub> nanowires by one-step self-catalysed evaporation growth. <i>CrystEngComm</i> , 2016, 18, 7147-7153.	2.6	6
6	Radiative transitions in highly doped and compensated chalcopyrites and kesterites: The case of $\text{Cu}_2\text{ZnSnS}_4$ . <i>Physical Review B</i> , 2014, 90, .	3.0	48
7	Comparison of fluctuating potentials and donor-acceptor pair transitions in a Cu-poor Cu <sub>2</sub> ZnSnS <sub>4</sub> based solar cell. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	34
8	Photoluminescence study of GaAs thin films and nanowires grown on Si(111). <i>Journal of Materials Science</i> , 2013, 48, 1794-1798.	3.7	19
9	Hopping conduction and persistent photoconductivity in Cu <sub>2</sub> ZnSnS <sub>4</sub> thin films. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 155107.	2.8	86
10	Structural and optical characterization of Mg-doped GaAs nanowires grown on GaAs and Si substrates. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	25
11	Photoluminescence and electrical study of fluctuating potentials in Cu <sub>2</sub> ZnSnS <sub>4</sub> -based thin films. <i>Physical Review B</i> , 2011, 84, .	3.2	138
12	Influence of Ge content on the optical properties of XandWcenters in dilute Si-Ge alloys. <i>Physical Review B</i> , 2011, 84, .	3.2	16